

MOSFET – Single, N-Channel, POWERTRENCH®

30 V, 11 A, 13 mΩ

FDMA7630

Description

This Device has been Designed To Provide Maximum Efficiency and Thermal Performance for synchronous buck converters. The low $R_{DS(on)}$ and gate charge provide excellent switching performance.

Features

- Max $R_{DS(on)} = 13 \text{ mΩ}$ at $V_{GS} = 10 \text{ V}$, $I_D = 11 \text{ A}$
- Max $R_{DS(on)} = 20 \text{ mΩ}$ at $V_{GS} = 4.5 \text{ V}$, $I_D = 9 \text{ A}$
- Low Profile – 0.8 mm Maximum – in the New Package MicroFET™ 2x2 mm
- Free from halogenated compounds and antimony oxides
- These Devices is Pb-Free, Halide Free and is RoHS Compliant

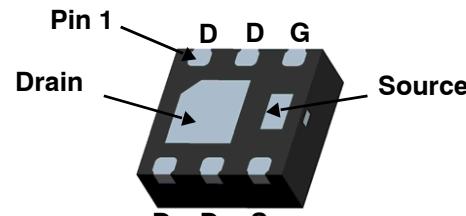
Typical Applications

- DC-DC Buck Converters

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$ unless otherwise noted

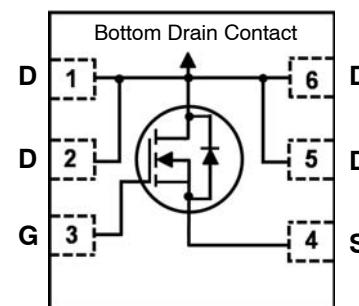
Symbol	Parameter	Value	Unit
V_{DSS}	Drain to Source Voltage	30	V
V_{GSS}	Gate to Source Voltage	± 20	V
I_D	Drain Current – Continuous $T_A = 25^\circ\text{C}$ (Note 1a) – Pulsed	11 24	A
P_D	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1)	24	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1)	0.9	
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

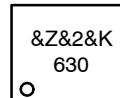


MicroFET 2X2 (Bottom View)

WDFN6 2X2, 0.65P
CASE 511CZ



MARKING DIAGRAM



&Z = Assembly Plant Code
&2 = Date Code (Year & Week)
&K = Lot Traceability Code
630 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping [†]
FDMA7630	WDFN-6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	52	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	145	°C/W

ELECTRICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
--------	-----------	-----------------	-----	-----	-----	------

Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}$	30	–	–	V
$\frac{\Delta V_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}, \text{Referenced to } 25^\circ\text{C}$	–	15	–	mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$	–	–	1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	–	–	100	nA

On Characteristics

$V_{GS(\text{th})}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	1.0	2.0	3.0	V
$\frac{\Delta V_{GS(\text{th})}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}, \text{Referenced to } 25^\circ\text{C}$	–	–6	–	mV/°C
$R_{DS(\text{on})}$	Static Drain–Source On–Resistance	$V_{GS} = 10 \text{ V}, I_D = 11 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 9 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 11 \text{ A}, T_J = 125^\circ\text{C}$	–	10	13	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_D = 11 \text{ A}$	–	36	–	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$	–	1020	1360	pF
C_{oss}	Output Capacitance		–	315	415	pF
C_{rss}	Reverse Transfer Capacitance		–	35	55	pF
R_g	Gate Resistance	–	1.7	–	–	Ω

Switching Characteristics (Note 2)

$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = 15 \text{ V}, I_D = 11 \text{ A}, V_{GS} = 10 \text{ V}, R_{\text{GEN}} = 6 \Omega$	–	8	15	ns
t_r	Rise Time		–	3	10	ns
$t_{d(off)}$	Turn–Off Delay Time		–	19	34	ns
t_f	Fall Time		–	3	10	ns
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ V} \text{ to } 10 \text{ V}$ $V_{DD} = 15 \text{ V}, I_D = 11 \text{ A}$	–	16	22	nC
		$V_{GS} = 0 \text{ V} \text{ to } 4.5 \text{ V}$ $V_{DD} = 15 \text{ V}, I_D = 11 \text{ A}$	–	8	10	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DD} = 15 \text{ V}, I_D = 11 \text{ A}$	–	3.0	–	nC
Q_{gd}	Gate to Drain “Miller” Charge		–	2.2	–	nC

Drain–Source Diode Characteristics and Maximum Ratings

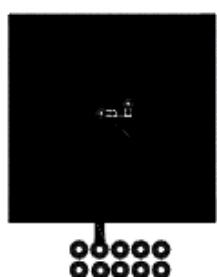
I_S	Maximum Continuous Drain–Source Diode Forward Current	–	–	2	A	
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 2 \text{ A}$ (Note 2)	–	0.8	1.2	V
t_{rr}	Reverse Recovery Time	$I_F = 11 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$	–	21	33	ns
Q_{rr}	Reverse Recovery Charge		–	6	12	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

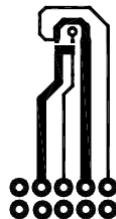
FDMA7630

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



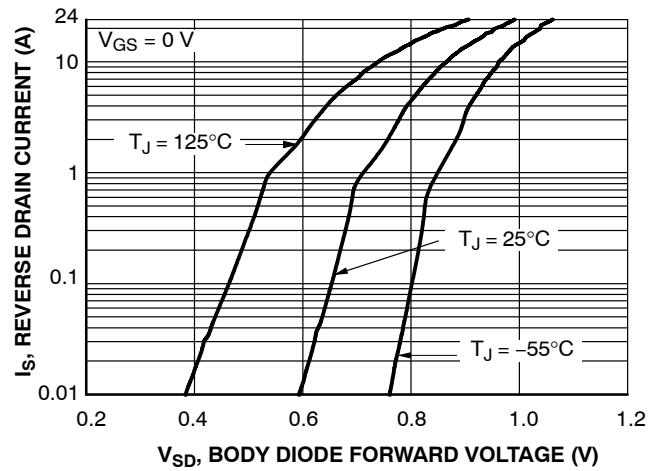
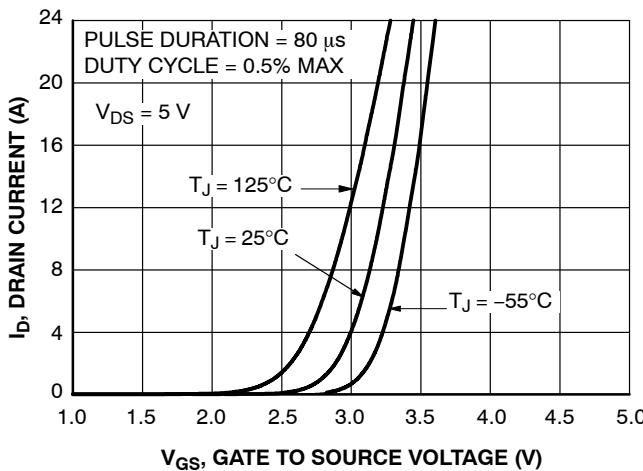
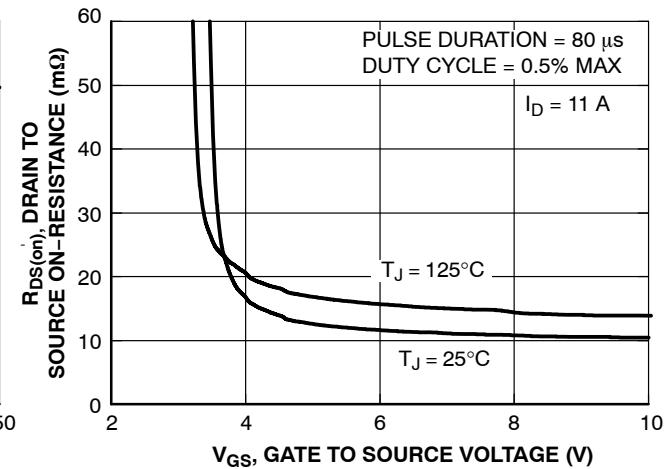
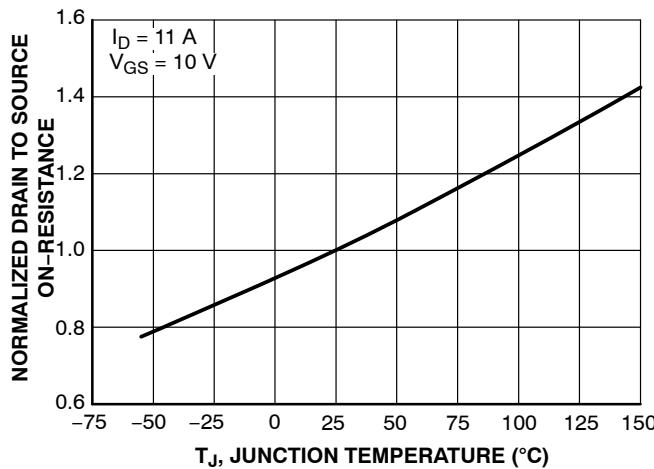
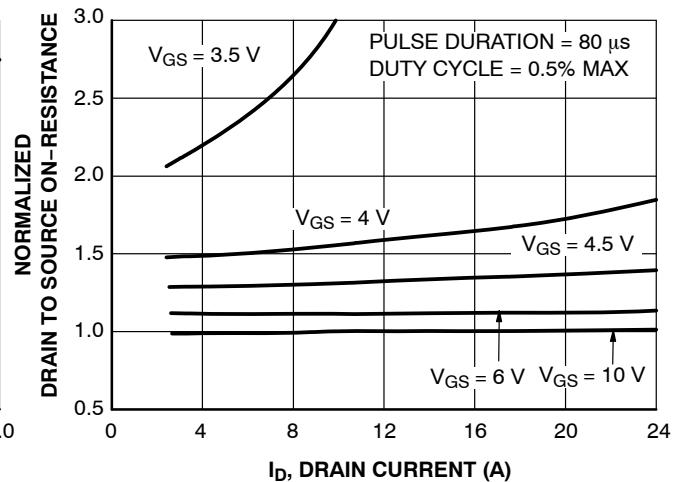
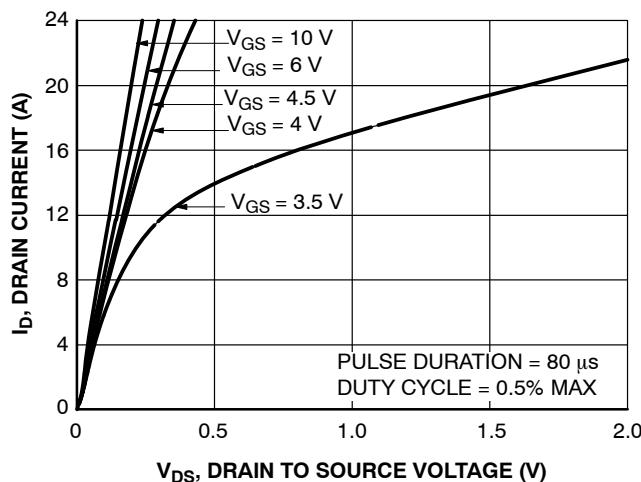
a. 52 °C/W when mounted on a 1 in² pad of 2 oz copper.



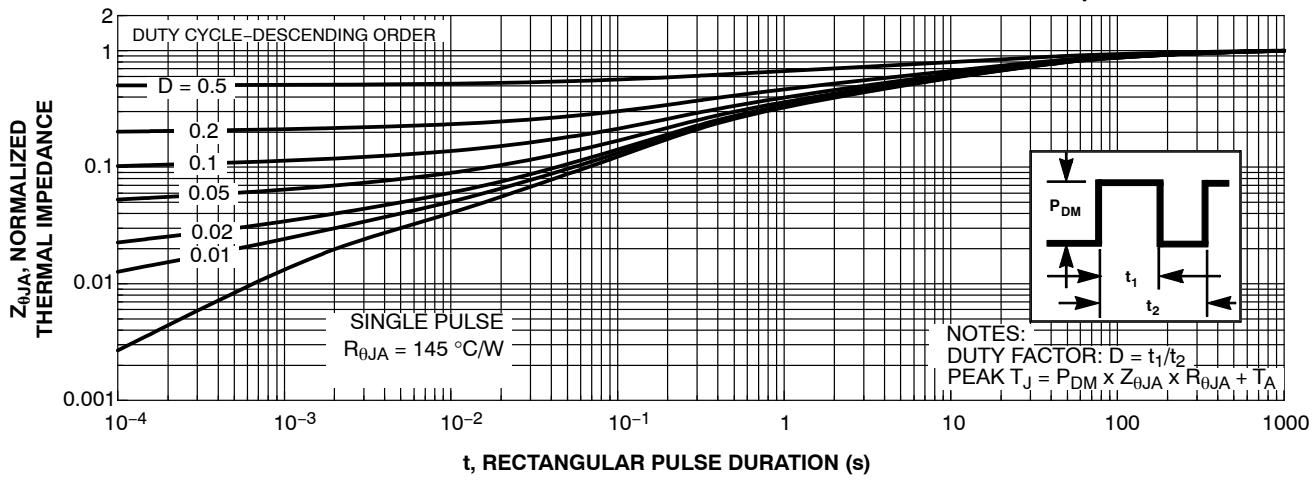
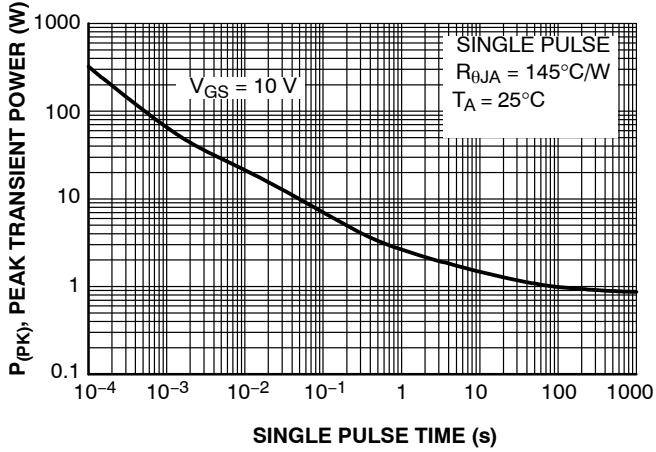
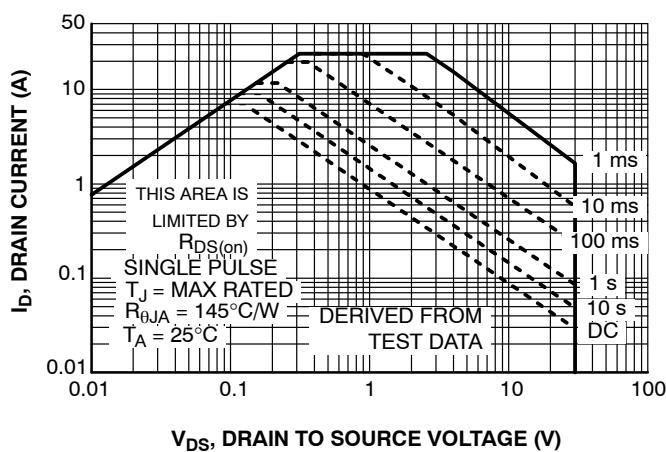
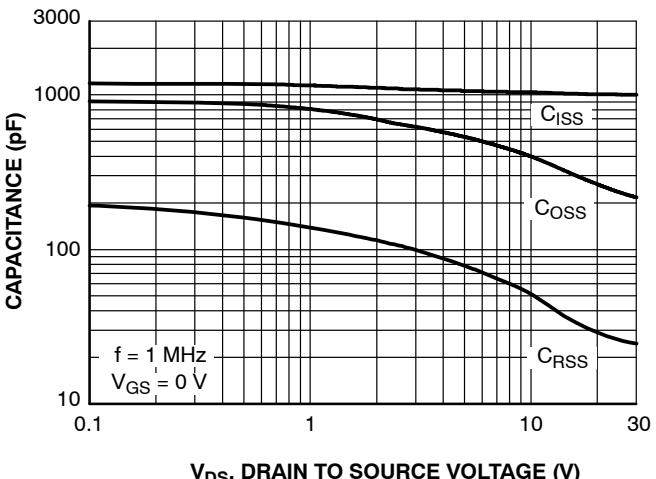
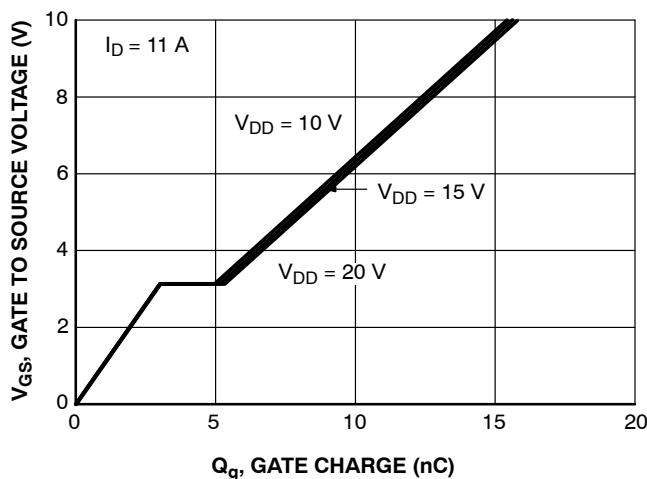
b. 145 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

TYPICAL CHARACTERISTICS



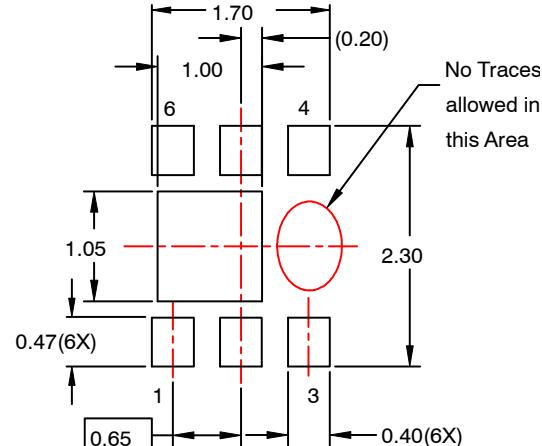
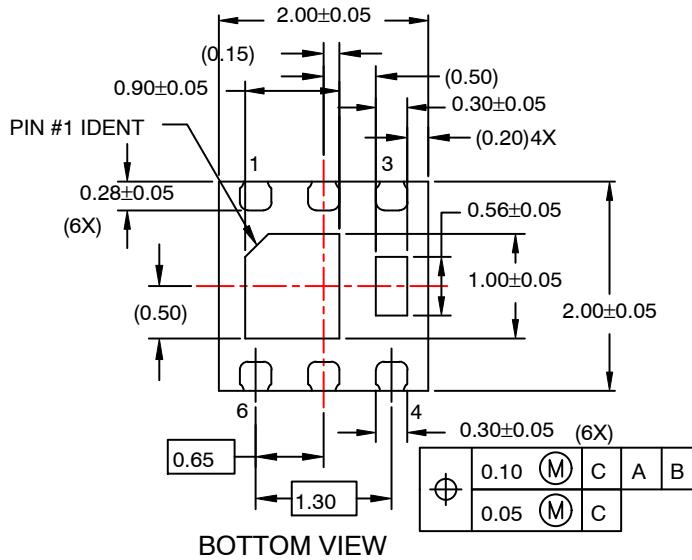
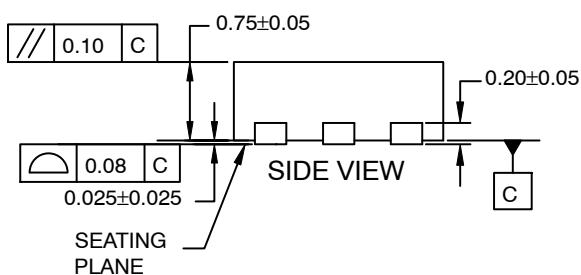
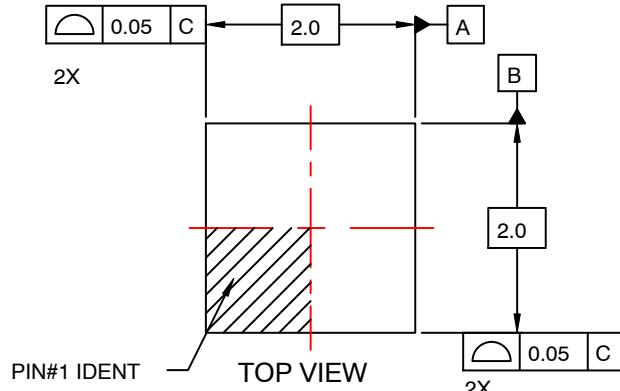
TYPICAL CHARACTERISTICS (CONTINUED)



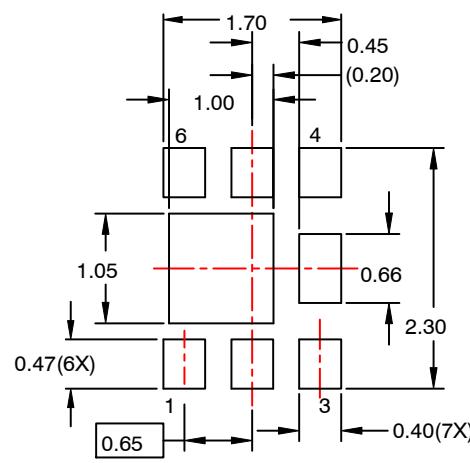
MicroFET is trademark of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries.

WDFN6 2x2, 0.65P
CASE 511CZ
ISSUE O

DATE 31 JUL 2016



RECOMMENDED
LAND PATTERN OPT 1



RECOMMENDED
LAND PATTERN OPT 2

NOTES:

- A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC MO-229 REGISTRATION
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

DOCUMENT NUMBER:	98AON13614G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	WDFN6 2X2, 0.65P	PAGE 1 OF 1

onsemi and **ONSEMI** are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

onsemi, **ONSEMI**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales

